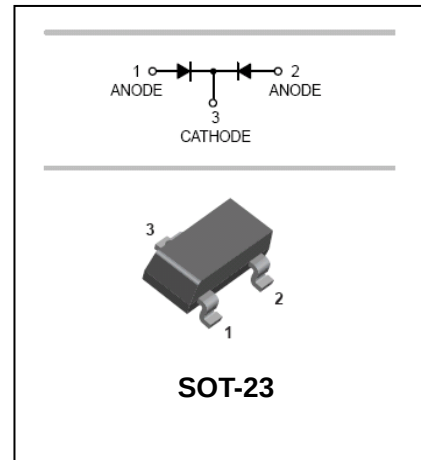


Low-leakage double diode

BAV170

FEATURES

- Plastic SMD package
- Low leakage current: typ. 3pA
- Switching time: typ. 0.8 ms
- Continuous reverse voltage: max. 75V
- Repetitive peak reverse voltage: max. 85V
- Repetitive peak forward current: max. 500mA.



APPLICATIONS

- Low-leakage current applications in surface mounted circuits.

ORDERING INFORMATION

Type No.	Marking	Package Code
BAV170	JX	SOT-23

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Characteristic	Symbol	Limits	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	85	V
DC Reverse Voltage	V_R	75	V
Forward Continuous Current single diode loaded double diode loaded	I_F	215 125	mA
repetitive peak forward current	I_{FRM}	500	mA
non-repetitive peak forward current square wave; $T_j=25^\circ\text{C}$ prior to surge; $t_p=1\mu\text{s}$ $t_p=1\text{ms}$ $t_p=1\text{s}$	I_{FSM}	4 1 0.5	A
Total Power Dissipation	P_{tot}	250	mW
Operating Junction Temperature Range	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-65 to +125	$^\circ\text{C}$

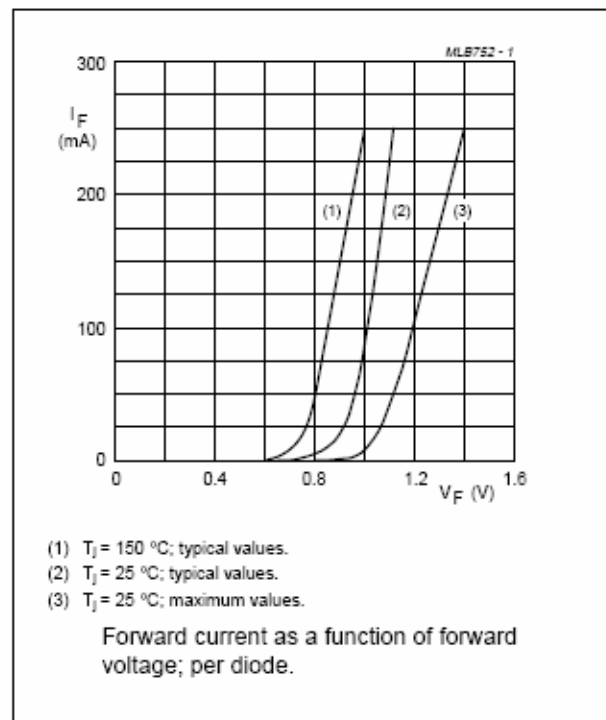
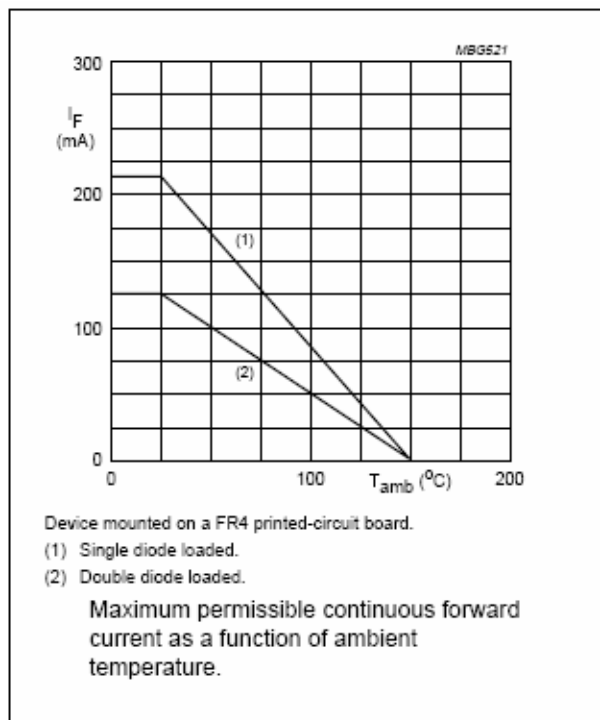
Low-leakage double diode

BAV170

ELECTRICAL CHARACTERISTICS @ $T_a=25^\circ\text{C}$ unless otherwise specified

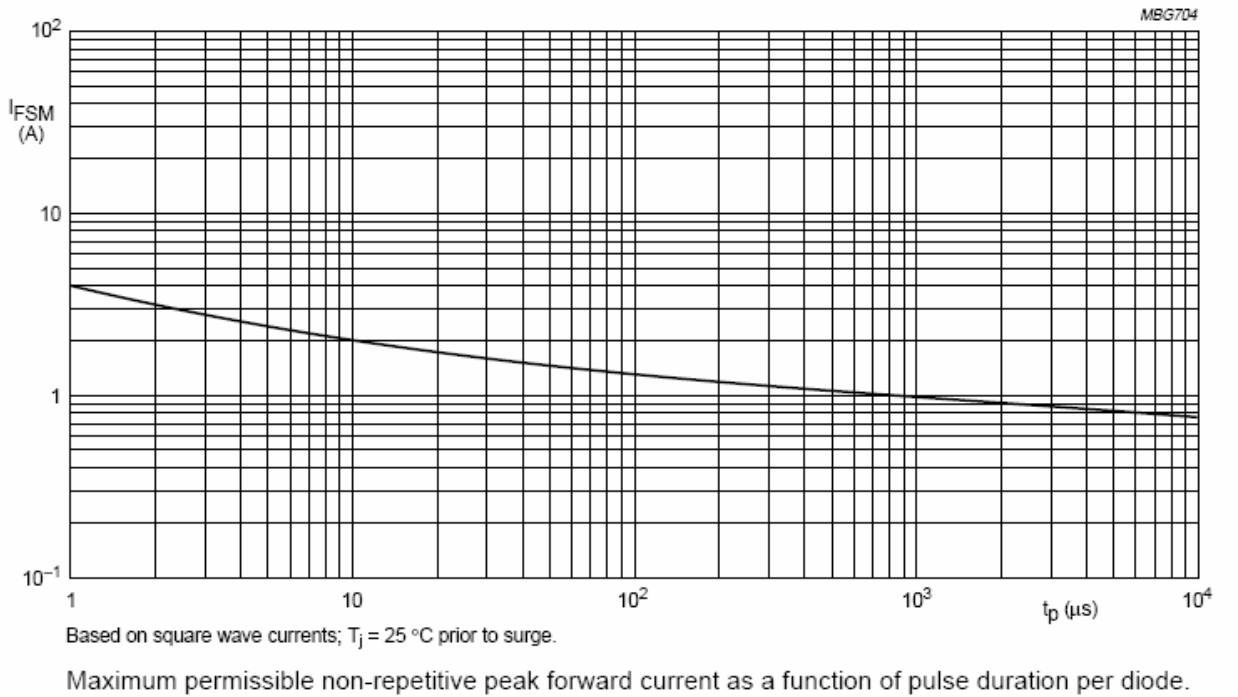
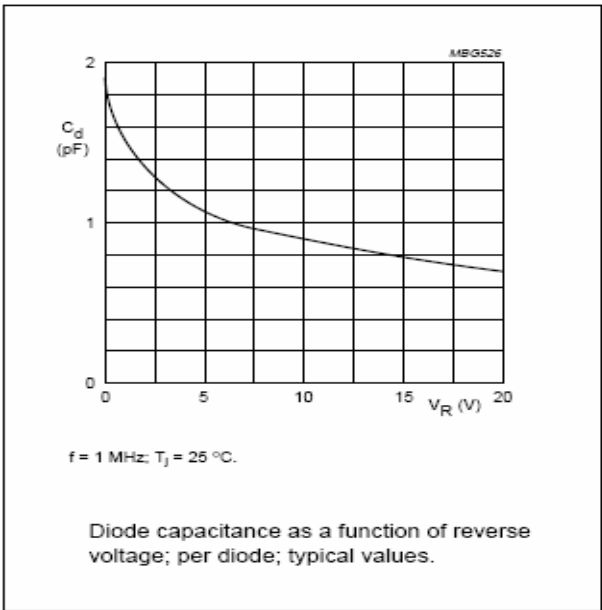
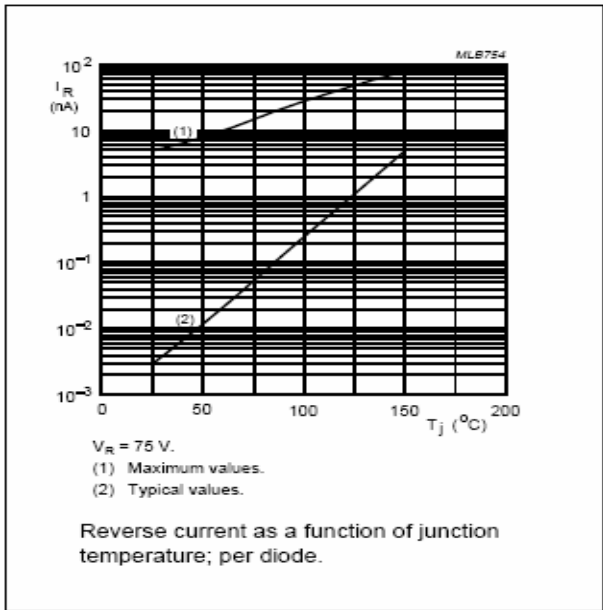
Characteristic	Symbol	Typ	MAX	UNIT	Test Condition
Forward Voltage	V_F		900 1000 1100 1250	mV	$I_F=1\text{mA}$ $I_F=10\text{mA}$ $I_F=50\text{mA}$ $I_F=100\text{mA}$
Reverse Leakage Current	I_R		5	nA	$V_R=75\text{V}$
Junction Capacitance	C_j		2.0	pF	$V_R=0\text{V}, f=1.0\text{MHz}$
Reverse Recovery Time	t_{rr}		3	μs	$I_F=I_R=10\text{mA}, t_{rr}=0.1 \cdot I_R$

TYPICAL CHARACTERISTICS @ $T_a=25^\circ\text{C}$ unless otherwise specified



Low-leakage double diode

BAV170



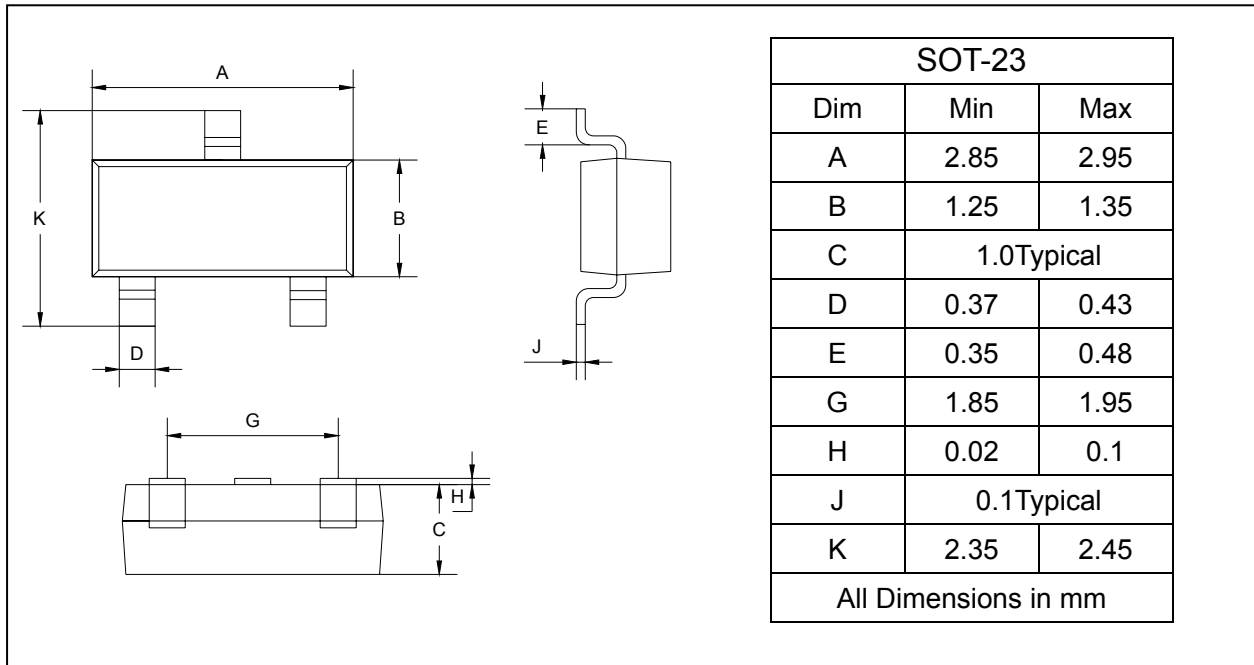
Low-leakage double diode

BAV170

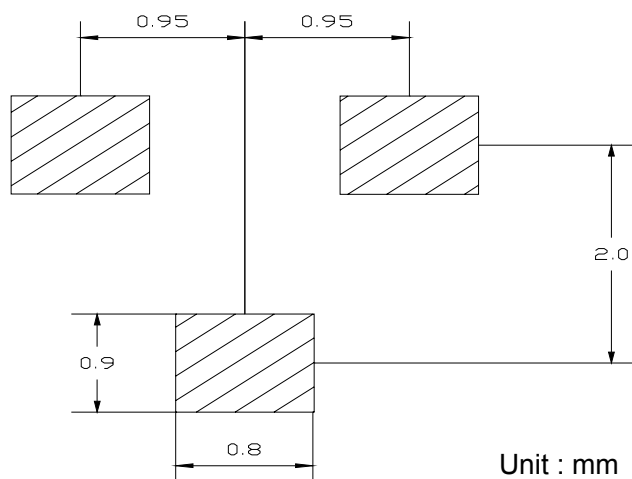
PACKAGE OUTLINE

Plastic surface mounted package

SOT-23



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
BAV170	SOT-23	3000/Tape&Reel